

WAFER PRODUCING METHOD

ABSTRACT OF THE DISCLOSURE

A peeling layer is formed by applying a laser beam only to a central region of a workpiece other than a peripheral region extending inward from the peripheral edge of the workpiece by a predetermined distance. In this case, the application of the laser beam does not form the peeling layer in the peripheral region of the workpiece, and the formation of an ablation trace on the outer peripheral surface of the workpiece is prevented. As a result, it is possible to reduce a probability of occurrence of chipping in the peripheral region of a wafer peeled off from the workpiece when the wafer is subjected to a post-process.

[Fig. 5A]